

ABSTRACT

A process for forming trenches with an oblique profile and rounded top corners, including the steps of: in a semiconductor wafer, through a first polymerizing etch, forming depressions delimited by rounded top corners; and through a second 5 polymerizing etch, opening trenches at the depressions. The second polymerizing etch is made in variable plasma conditions, so that the trenches have oblique walls with a constant slope.